In the Claims

Amendments to the Claims:

1. (currently amended) A die, comprising:

a substrate; and

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one two or more different types of pillar structures formed over the substrate

in a pattern; at least one of the one two or more different types of pillar structures

are bi-layer having a lower high-melting-point non-solder portion and an upper

solder material portion over and in substantial contact with only an upper surface

of the lower high-melting point non-solder portion; wherein the lower high-

melting-point non-solder portion does not melt during a reflow process to form the

one two or more different types of pillar structures.

2. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures have has a rectangular shape, a round

shape, a ring shape, a wall-like shape or a spline shape.

3. (currently amended) The die of claim 1, wherein the at least one of the two or

more <u>different types of</u> pillar structures <u>have</u> <u>has</u> a rectangular shape with a length

of from about 789.0 to 1289.0 μm and a width of about 289.0 μm .

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4. (currently amended) The die of claim 1, wherein the at least one of the two or

more <u>different types of</u> pillar structures have has a rectangular shape with a length

of about 789.0 μm and a width of about 289.0 μm.

5. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures have has a rectangular shape with a length

of about 1289.0 μm and a width of about 289.0 μm.

6. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures have has a rectangular shape and the two

or more different types of pillar structures are spaced apart lengthwise by about

 $500.0~\mu m$ center-to-center and by about 211.0 μm end-to-end.

7. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures have has a round shape with a diameter of

about 289.0 μm.

8. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures have has a round shape with a diameter of

about 289.0 µm; the two or more different types of pillar structures being arranged

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at least in part in rows and columns with the adjacent round pillar structures being

spaced apart by about 500.0 μm.

9. (original) The die of claim 1, wherein the pillar structure pattern includes a series

of rows and columns.

10. (previously presented) The die of claim 1, wherein the pillar structure pattern

includes a series of rows and columns; the pillar structures arranged in the series of

rows and columns are spaced apart lengthwise by about 500.0 µm center-to-center

in the columns and are spaced apart about 211.0 µm end-to-end.

11. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures include includes at least one wall-shaped

pillar structure.

12. (currently amended) The die of claim 1, wherein the at least one of the two or

more different types of pillar structures include includes at least one wall-shaped

pillar structure forming a square.

13. (original) The die of claim 1, including a pillar wall.

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14. (canceled)
15. (canceled)
16. (previously presented) The die of claim 1, wherein the lower high-melting-point non-solder portion is comprised of copper coated with oxide, chromium or nickel.
17. (canceled)
18. (canceled)
19. (previously presented) The die of claim 1, wherein the upper solder material portion is comprised of: from about 60 to 70% tin and from about 30 to 40% lead; about 63% tin and 37% lead; about 99% tin and SnAg; or 100%tin.
20. (previously presented) The die of claim 1, wherein the solder material portion is
comprised of:
about 63% tin and 37% lead; or

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100%tin.

21. (currently amended) The die of claim 1, wherein the pillar structures having

each have a total height of from about 60 to 150 µm.

22. (currently amended) The die of claim 1, wherein the pillar structures having

each have a total height of about 100 μm.

23. (original) The die of claim 1, wherein the die is used in Surface Acoustic Wave

devices and in MEM devices.

24. (currently amended) A die, comprising:

a substrate; and

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one two or more different types of pillar structures formed over the substrate

in a pattern; the one two or more different types of pillar structures having a

rectangular shape, a round shape, a ring shape, a wall-like shape or a spline shape;

at least one of the one two or more different types of pillar structures are bi-layer

having a lower high-melting-point non-solder portion and an coextensive upper

solder material portion over and in substantial contact with only an upper surface

of the lower high-melting point non-solder portion; wherein the lower high-

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10 melting-point non-solder portion does not melt during a reflow process to form the

one two or more different types of pillar structures.

25. (currently amended) The die of claim 24, wherein the at least one of the two or

more different types of pillar structures have has a rectangular shape with a length

of from about 789.0 to 1289.0 μ m and a width of about 289.0 μ m.

26. (currently amended) The die of claim 24, wherein the at least one of the two or

more different types of pillar structures have has a rectangular shape with a length

of about 789.0 µm and a width of about 289.0 µm.

27. (currently amended) The die of claim 24, wherein the at least one of the two or

more different types of pillar structures have has a rectangular shape with a length

of about 1289.0 μm and a width of about 289.0 μm .

28. (currently amended) The die of claim 24, wherein the at least one of the two or

more <u>different types of</u> pillar structures <u>have</u> <u>has</u> a rectangular shape and the <u>two</u>

or more different types of pillar structures are spaced apart lengthwise by about

 $500.0~\mu m$ center-to-center and by about 211.0 μm end-to-end.

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29. (currently amended) The die of claim 24, wherein the at least one of the two or

more different types of pillar structures have has a round shape with a diameter of

about 289.0 μm.

30. (currently amended) The die of claim 24, wherein the at least one of the two or

more different types of pillar structures have has a round shape with a diameter of

about 289.0 µm; the two or more different types of pillar structures being arranged

at least in part in rows and columns with the adjacent round pillar structures being

spaced apart by about 500.0 μm.

31. (original) The die of claim 24, wherein the pillar structure pattern includes a

series of rows and columns.

32. (previously presented) The die of claim 24, wherein the pillar structure pattern

includes a series of rows and columns; the pillar structures arranged in the series of

rows and columns are spaced apart lengthwise by about 500.0 µm center-to-center

in the columns and are spaced apart about 211.0 μm end-to-end.

33. (currently amended) The die of claim 24, wherein the one two or more different

types of pillar structures include at least one wall-shaped pillar structure.

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34. (currently amended) The die of claim 24, wherein the one two or more different types of pillar structures include at least one wall-shaped pillar structure forming a square.

35. (original) The die of claim 24, including a pillar wall.

36. (canceled)

37. (canceled)

38. (previously presented) The die of claim 24, wherein the lower high-melting-point non-solder portion is comprised of copper coated with oxide, chromium or nickel.

39. (canceled)

40. (canceled)

41. (previously presented) The die of claim 24, wherein the upper solder material portion is comprised of:

from about 60 to 70% tin and from about 30 to 40% lead;

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about 63% tin and 37% lead;

about 99% tin and SnAg; or

100%tin.

42. (previously presented) The die of claim 24, wherein the upper solder material

portion is comprised of:

about 63% tin and 37% lead; or

100%tin.

43. (currently amended) The die of claim 24, wherein the pillar structures having

each have a total height of from about 60 to 150 μm .

44. (currently amended) The die of claim 24, wherein the pillar structures having

each have a total height of about 100 μm.

45. (original) The die of claim 24, wherein the die is used in Surface Acoustic Wave

devices and in MEM devices.

46. (currently amended) A method of forming a die, comprising the steps:

providing a substrate; and

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forming one two or more different types of pillar structures over the

substrate in a pattern; at least one of the one two or more different types of pillar

structures are is bi-layer having a lower high-melting-point non-solder portion and

an coextensive upper solder material portion over and in substantial contact with

only an upper surface of the lower high-melting point non-solder portion; wherein

the lower high-melting-point non-solder portion does not melt during a reflow

process to form the one two or more different types of pillar structures.

47. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures have has a rectangular shape, a round

shape, a ring shape, a wall-like shape or a spline shape.

48. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures have has a rectangular shape with a

length of from about 789.0 to 1289.0 μm and a width of about 289.0 μm.

49. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures have has a rectangular shape with a

length of about 789.0 μm and a width of about 289.0 μm.

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50. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures have has a rectangular shape with a

length of about 1289.0 μm and a width of about 289.0 μm .

51. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures have has a rectangular shape and the two

or more different types of pillar structures are spaced apart lengthwise by about

 $500.0 \mu m$ center-to-center and by about $211.0 \mu m$ end-to-end.

52. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures have has a round shape with a diameter

of about 289.0 µm.

53. (currently amended) The method of claim 46, wherein the at least one of the two

or more <u>different types of</u> pillar structures <u>have</u> <u>has</u> a round shape with a diameter

of about 289.0 µm; the two or more different types of pillar structures being

arranged at least in part in rows and columns with the adjacent round pillar

structures being spaced apart by about 500.0 μm .

54. (original) The method of claim 46, wherein the pillar structure pattern includes a

series of rows and columns.

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55. (previously presented) The method of claim 46, wherein the pillar structure

pattern includes a series of rows and columns; the pillar structures arranged in the

series of rows and columns are spaced apart lengthwise by about 500.0 µm center-to-

center in the columns and are spaced apart about 211.0 µm end-to-end.

56. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures include includes at least one wall-shaped

pillar structure.

57. (currently amended) The method of claim 46, wherein the at least one of the two

or more different types of pillar structures includes at least one wall-shaped

pillar structure forming a square.

58. (original) The method of claim 46, including a pillar wall.

59. (canceled)

60. (canceled)

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61. (previously presented) The method of claim 46, wherein the lower high-melting-point non-solder portion is comprised of copper coated with oxide, chromium or nickel.

62. (canceled)

63. (canceled)

64. (previously presented) The method of claim 46, wherein the upper solder material portion is comprised of:

from about 60 to 70% tin and from about 30 to 40% lead;

about 63% tin and 37% lead;

about 99% tin and SnAg; or

100%tin.

65. (previously presented) The method of claim 46, wherein the upper solder material portion is comprised of:

about 63% tin and 37% lead; or

100%tin.

66. (currently amended) The method of claim 46, wherein the pillar structures having each have a total height of from about 60 to 150 μ m.

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67. (currently amended) The method of claim 46, wherein the pillar structures

having each have a total height of about 100 µm.

68. (original) The method of claim 46, wherein the die formed is used in Surface

Acoustic Wave devices and in MEM devices.

69. (previously presented) The method of claim 1, wherein the lower high-melting-

point non-solder portion is comprised of copper.

70. (previously presented) The method of claim 24, wherein the lower high-melting-

point non-solder portion is comprised of copper.

71. (previously presented) The method of claim 46, wherein the lower high-melting-

point non-solder portion is comprised of copper.